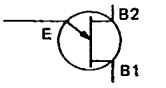
PN Unijunction Transistors
Silicon Unijunction Transistors

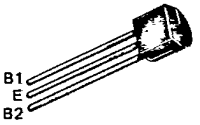
2N4870
2N4871

. . . designed for pulse and timing circuits, sensing circuits, and thyristor trigger circuits. These devices feature:

- Low Peak Point Current — 1 μA Typical
- Low Emitter Reverse Current — 5 nA Typical
- Passivated Surface for Reliability and Uniformity
- One-Piece Injection-Molded Unibloc‡ Plastic Package for Economy and Reliability
- High η for greater bandwidth

PN UJTs





CASE 29-04
(TO-226AA)
STYLE 9

MAXIMUM RATINGS (T_A = 25° unless otherwise noted.)

Rating	Symbol	Value	Unit
RMS Power Dissipation, Note 1	P_D	300	mW
RMS Emitter Current	I_e	50	mA
Peak-Pulse Emitter Current, Note 2	i_e	1.5	Amp
Emitter Reverse Voltage	V_{B2E}	30	Volts
Interbase Voltage, Note 3	V_{B2B1}	35	Volts
Operating Junction Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

Notes: 1. Derate 3 mW/°C increase in ambient temperature.
2. Duty cycle ≤ 1%, PRR = 10 PPS (see Figure 5).
3. Based upon power dissipation at T_A = 25°C.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Fig. No.	Symbol	Min	Typ	Max	Unit
Intrinsic Standoff Ratio, Note 1 (V_{B2B1} = 10 V)	2N4870	4, 7	η	0.56	—	0.75	—
	2N4871			0.70	—	0.85	
Interbase Resistance (V_{B2B1} = 3 V, I_E = 0)		10, 11	R_{BB}	4	6	9.1	k ohms
Interbase Resistance Temperature Coefficient (V_{B2B1} = 3 V, I_E = 0, T_A = −65 to +125°C)		11	αR_{BB}	0.10	—	0.90	%/°C
Emitter Saturation Voltage, Note 2 (V_{B2B1} = 10 V, I_E = 50 mA)			$V_{EB1(sat)}$	—	2.5	—	Volts
Modulated Interbase Current (V_{B2B1} = 10 V, I_E = 50 mA)			$I_{B2(mod)}$	—	15	—	mA
Emitter Reverse Current (V_{B2E} = 30 V, I_{B1} = 0)		6	I_{EB2O}	—	0.005	1	μA
Peak-Point Emitter Current (V_{B2B1} = 25 V)		8, 9	I_P	—	1	5	μA
Valley-Point Current, Note 2 (V_{B2B1} = 20 V, R_{B2} = 100 ohms)	2N4870	12, 13	I_V	2	5	—	mA
	2N4871			4	7	—	
Base-One Peak Pulse Voltage	2N4870	3, 16	V_{OB1}	3	6	—	Volts
	2N4871			5	8	—	

Notes: 1. η, Intrinsic standoff ratio, is defined in terms of the peak-point voltage, V_P, by means of the equation: $V_P = \eta V_{B2B1} + V_F$, where V_F is about 0.49 volt at 25°C @ I_F = 10 μA and decreases with temperature at about 2.5 mV/°C. The test circuit is shown in Figure 4. Components R_1, C_1, and the UJT form a relaxation oscillator; the remaining circuitry serves as a peak-voltage detector. The forward drop of Diode D_1 compensates for V_R. To use, the "cal" button is pushed, and R_3 is adjusted to make the current meter, M_1, read full scale. When the "cal" button is released, the value of η is read directly from the meter, if full scale on the meter reads 1.

2. Use pulse techniques: PW ≈ 300 μs, duty cycle ≤ 2% to avoid internal heating, which may result in erroneous readings.

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FIGURE 1 – UNIJUNCTION TRANSISTOR SYMBOL AND NOMENCLATURE

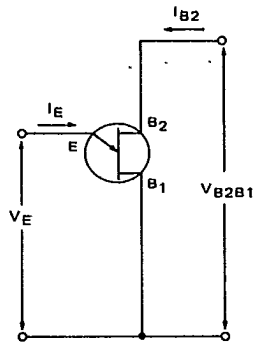

FIGURE 2 – STATIC EMITTER CHARACTERISTICS CURVES

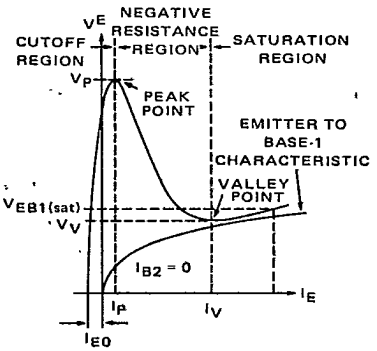

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FIGURE 3 – V_{OB1} TEST CIRCUIT

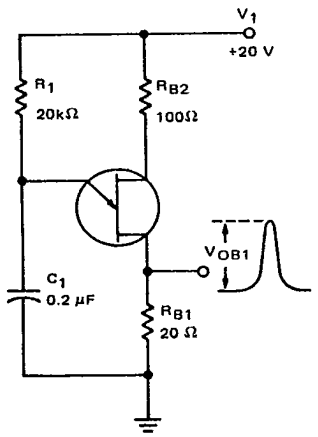
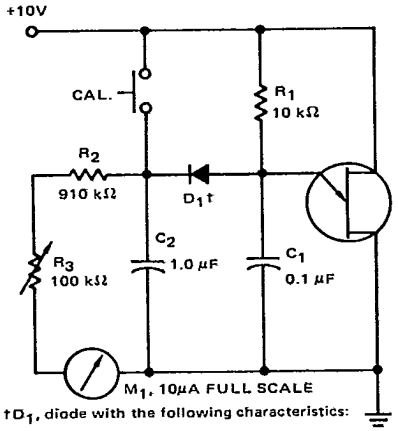


FIGURE 4 – η TEST CIRCUIT

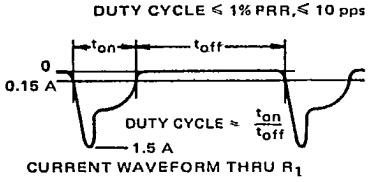


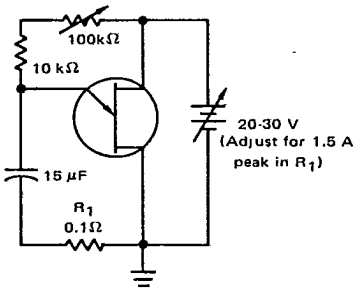
†D_1, diode with the following characteristics:

$V_F = 0.49$ V @ $I_F = 10$ μA

$I_R \leq 2.0$ μA @ $V_R = 20$ V

FIGURE 5 – PRR TEST CIRCUIT AND WAVEFORM





TYPICAL CHARACTERISTICS

FIGURE 6 – EMITTER REVERSE CURRENT

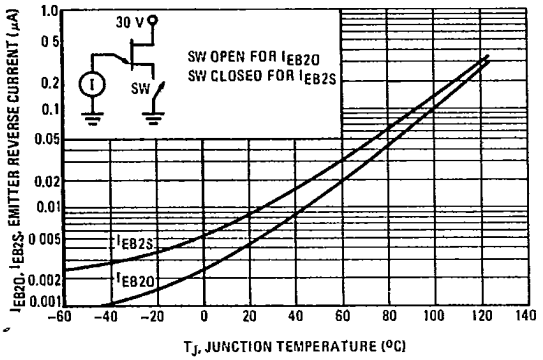
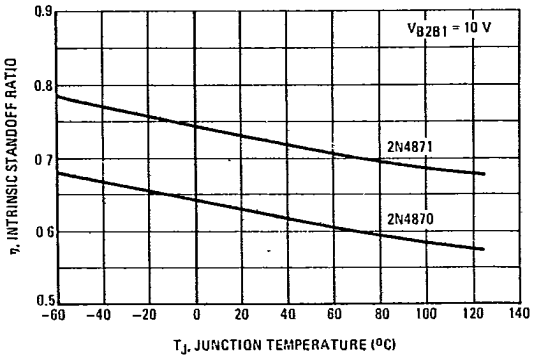


FIGURE 7 – INTRINSIC STANDOFF RATIO



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PEAK POINT CURRENT

FIGURE 8 – EFFECT OF VOLTAGE

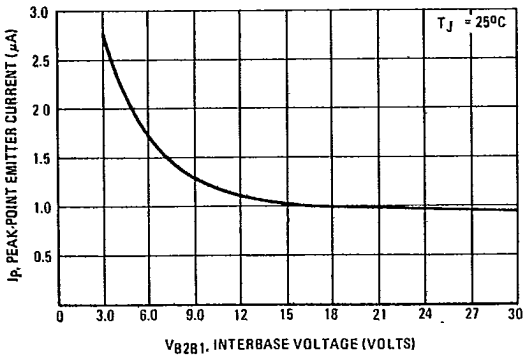
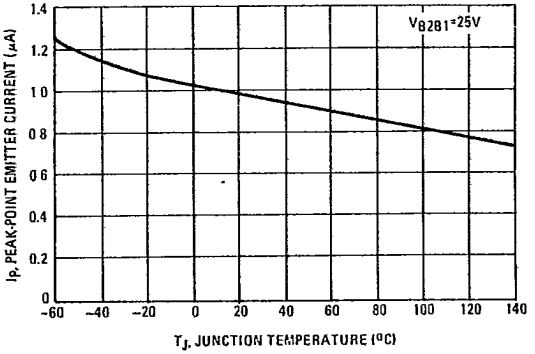


FIGURE 9 – EFFECT OF TEMPERATURE



INTERBASE RESISTANCE

FIGURE 10 – EFFECT OF VOLTAGE

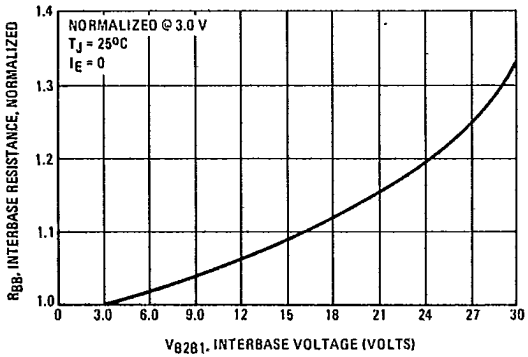
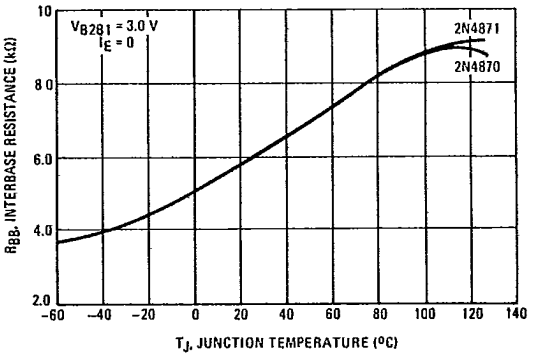


FIGURE 11 – EFFECT OF TEMPERATURE



TYPICAL CHARACTERISTICS

VALLEY CURRENT

FIGURE 12 – EFFECT OF VOLTAGE

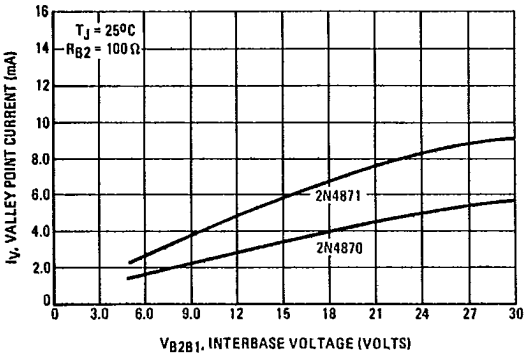
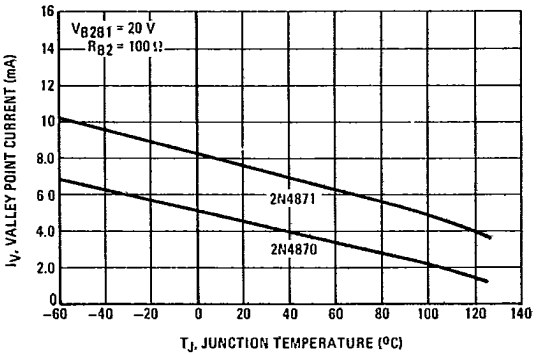


FIGURE 13 – EFFECT OF TEMPERATURE



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VALLEY VOLTAGE

FIGURE 14 – EFFECT OF VOLTAGE

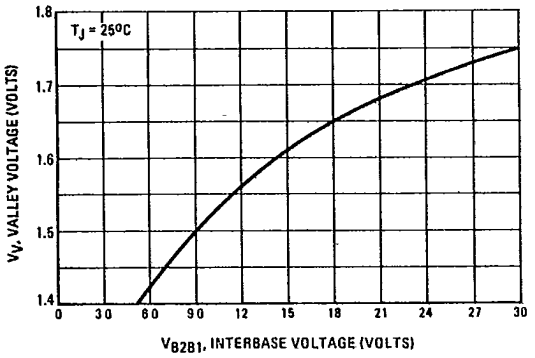

FIGURE 15 – EFFECT OF TEMPERATURE

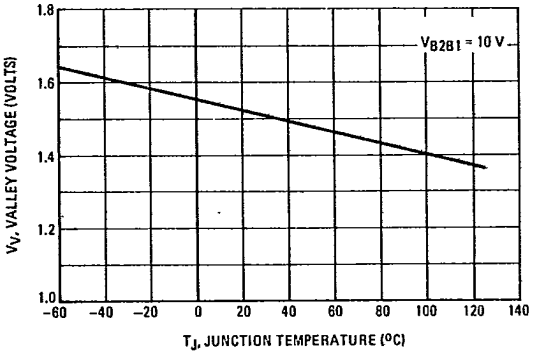

FIGURE 16 – OUTPUT VOLTAGE